

2824



Docket No.: 49657-862

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#1513
Web
1-11-03

In re Application of

Naoki TSUJI

Serial No.: 09/745,468

Group Art Unit: 2824

Filed: December 26, 2000

Examiner: B. Owens

For: SEMICONDUCTOR DEVICE AND A PRODUCTION METHOD FOR THE SAME

AMENDMENT

Commissioner for Patents
Washington, DC 20231

Sir:

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The following Amendment and Remarks are submitted in response to the Office
Action dated October 2, 2002.

IN THE CLAIMS:

Please amend claim 1 as follows.

1. (Twice Amended) A semiconductor device comprising:

a first region where first transistors each having a first gate oxide film of a first thickness is formed;

a second region, adjacent to the first region, where second transistors each having a second gate oxide film of a second thickness are formed;

trench isolation patterns formed selectively within said first and second regions and extending continuously in a first direction; and